

ABSTRACT

5 A reflective mask blank that is a material for a reflective mask used in EUV
lithography using EUV light as the exposure light, including a substrate, a multilayer
reflection film that is formed on one main surface of the substrate and reflects the exposure
light, and an absorber film that is formed on the multilayer reflection film and absorbs the
exposure light, the absorber film being a single layer consisting of a first layer, or a
10 plurality of layers consisting of, from the substrate side, a first layer and a second layer, the
first layer being composed of tantalum and nitrogen and containing 55 to 70 at% of
tantalum and 30 to 45 at% of nitrogen, the second layer being composed of tantalum and
nitrogen, and oxygen of not more than 40 at%.

[Fig. 1]